Please **AMEND** claim 30, as follows.

1-17. (Previously Cancelled)

18. (Previously Amended) An apparatus for depositing a layer on a substrate for a liquid crystal device, comprising:

a load lock chamber receiving a substrate having a gate wire pattern formed thereon;

a preheat chamber receiving the substrate from said load lock chamber and heating the substrate before deposition;

a deposition chamber depositing a gate insulating layer, an amorphous silicon layer and a doped amorphous silicon layer by chemical vapor deposition; and

a sputter chamber depositing a metal layer on the doped amorphous silicon layer by sputtering,

wherein the substrate is transferred from said deposition chamber to said sputter chamber in a vacuum, and

wherein said load lock chamber, said preheat chamber, said deposition chamber and said sputter chamber are arranged in series.

18-29. (Previously Cancelled)

30. (Currently Amended) An apparatus for manufacturing a liquid crystal display, comprising:

a load lock chamber for receiving a substrate;

a preheat chamber for heating the substrate;

a first deposition chamber for depositing a gate insulating layer and an amorphous silicon layer on the gate wire pattern;

a second deposition chamber for depositing a doped amorphous silicon layer on the substrate;

a sputter chamber for depositing a metal layer on the doped amorphous silicon layer; and

a vacuum passage for transferring the substrate in a vacuum from said second deposition chamber to said sputter chamber to prevent oxidization of an upper surface of the doped amorphous silicon layer,

wherein said load lock chamber, said preheat chamber, said first deposition chamber, said second deposition chamber, said vacuum passage and said sputter chamber are arranged in series.

31. (Previously added) The deposition apparatus of claim 30, wherein the substrate has a gate wire pattern formed thereon.

32. (Previously Cancelled)

33. (Previously Amended) The deposition apparatus of claim 30, wherein said first deposition chamber and said second deposition chamber are chemical vapor deposition (CVD) chambers.

34. (Previously Added) The deposition apparatus of claim 31, wherein the metal layer comprises chromium (Cr).

35. (Previously Added) The deposition apparatus of claim 30, wherein the gate insulating layer is formed at a thickness between 3000 Å to 6000 Å, the amorphous silicon layer is formed at a thickness between 1000 Å to 3000 Å, and the doped amorphous silicon layer is formed at a thickness of 200 Å to 1000 Å.